

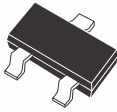
[查询CMPT918供应商](#)

[捷多邦, 专业PCB打样工厂, 24小时加急出货](#)

# Central Semiconductor Corp.

**CMPT918**

**NPN SILICON RF TRANSISTOR**



**SOT-23 CASE**

## DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT918 type is an NPN silicon RF transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high frequency (VHF/UHF) amplifier and oscillator applications.

**Marking code is C3B.**

## MAXIMUM RATINGS (T<sub>A</sub>=25°C)

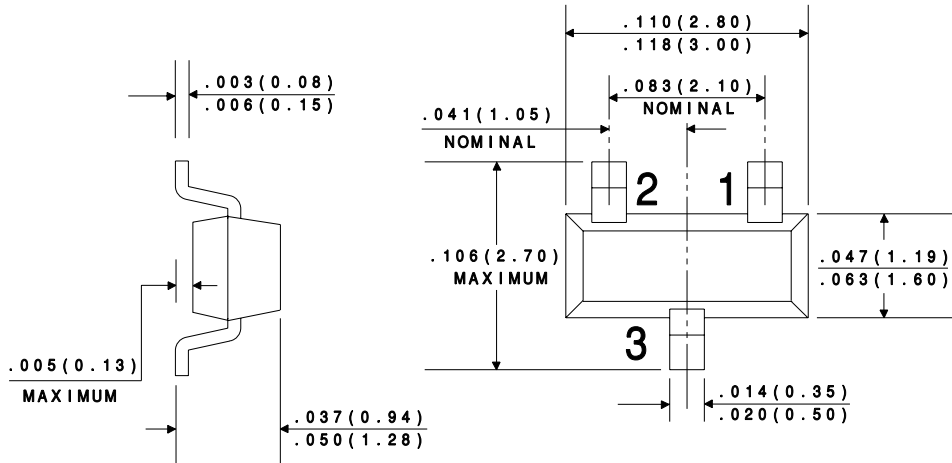
	SYMBOL		UNITS
Collector-Base Voltage	V <sub>CB0</sub>	30	V
Collector-Emitter Voltage	V <sub>CEO</sub>	15	V
Emitter-Base Voltage	V <sub>EBO</sub>	3.0	V
Collector Current	I <sub>C</sub>	50	mA
Power Dissipation	P <sub>D</sub>	350	mW
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	θ <sub>JA</sub>	357	°C/W

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I <sub>CB0</sub>	V <sub>CB</sub> =15V		10	nA
BV <sub>CB0</sub>	I <sub>C</sub> =1.0μA	30		V
BV <sub>CEO</sub>	I <sub>C</sub> =3.0mA	15		V
BV <sub>EBO</sub>	I <sub>E</sub> =10μA	3.0		V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1.0mA		0.4	V
V <sub>BE(SAT)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1.0mA		1.0	V
h <sub>FE</sub>	V <sub>CE</sub> =1.0V, I <sub>C</sub> =3.0mA	20		
f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =4.0mA, f=100MHz	600		MHz
C <sub>ob</sub>	V <sub>CB</sub> =0V, I <sub>E</sub> =0, f=1.0MHz		3.0	pF
C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1.0MHz		1.7	pF
C <sub>ib</sub>	V <sub>EB</sub> =0.5V, I <sub>C</sub> =0, f=1.0MHz		2.0	pF
P <sub>out</sub>	V <sub>CB</sub> =15V, I <sub>C</sub> =8.0mA, f=500MHz	30		mW
G <sub>ps</sub>	V <sub>CB</sub> =12V, I <sub>C</sub> =6.0mA, f=200MHz	11		dB
NF	V <sub>CE</sub> =6.0V, I <sub>C</sub> =1.0mA, R <sub>S</sub> =50Ω, f=60MHz		6.0	dB



All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR